**Product data sheet** 

# 1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO92) plastic package intended for use in low power SMPS emitter switching circuits.

## 2. Features and benefits

- Fast switching
- · High base current drive capability
- High voltage capability
- · Very low switching and conduction losses

## 3. Applications

- Emitter-switched low power SMPS circuits
- Self Oscillating Power Supplies
- AC-DC converters
- DC-AC inverters

# 4. Pinning information

**Table 1. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		В
3	В	base		- <b>/</b>
			3 2 1 TO-92 (SOT54)	sym123

## 5. Ordering information

**Table 2. Ordering information** 

Type number	Package			
	Name	Description	Version	
TB100	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54	

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# 6. Marking

### Table 3. Marking codes

Type number	Marking code
TB100	TB100

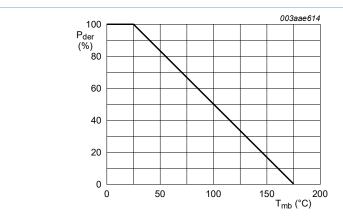
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# 7. Limiting values

## **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	700	V
$V_{CBO}$	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
I <sub>C</sub>	collector current	DC	-	1	Α
I <sub>CM</sub>	peak collector current		-	2	Α
$I_B$	base current		-	0.5	Α
I <sub>BM</sub>	peak base current		-	3	Α
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>	-	2	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig. 1. Normalized total power dissipation as a function of mounting base temperature

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## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead		-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; lead length = 4 mm; Fig. 2	-	150	-	K/W

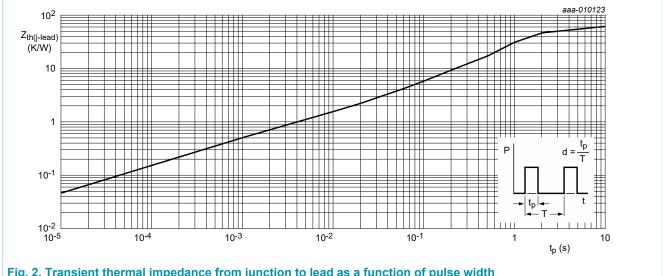


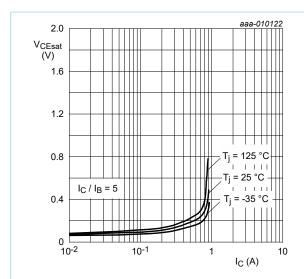
Fig. 2. Transient thermal impedance from junction to lead as a function of pulse width

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## 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
I <sub>CES</sub>	collector-emitter cut-off	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V	-	8.0	100	μA
	current (base shorted)	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	2	500	μA
I <sub>EBO</sub>	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	0.05	100	μA
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 0.75 \text{ A}$ ; $I_B = 0.15 \text{ A}$ ; $T_{lead} = 25 ^{\circ}\text{C}$ ; Fig. 3	-	0.24	1	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 0.75 \text{ A}$ ; $I_B = 0.15 \text{ A}$ ; $T_{lead} = 25 ^{\circ}\text{C}$ ; Fig. 4	-	0.93	1.3	V
h <sub>FE</sub>	DC current gain	$I_C$ = 10 mA; $V_{CE}$ = 5 V; $T_{lead}$ = 25 °C; Fig. 5; Fig. 6	12	22	32	
		$I_C$ = 100 mA; $V_{CE}$ = 5 V; $T_{lead}$ = 25 °C; Fig. 5; Fig. 6	14	24	34	
		$I_C = 0.75 \text{ A}; V_{CE} = 5 \text{ V}; T_{lead} = 25 ^{\circ}\text{C};$ Fig. 5; Fig. 6	12	15.5	20	
Dynamic ch	aracteristics (resistive loa	d)				
ts	storage time	I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.2 A; I <sub>Boff</sub> = -0.2 A;	-	2	-	μs
t <sub>f</sub>	fall time	$R_L = 75 \Omega$ ; $V_{BB} = -4 V$ ; $T_{lead} = 25 °C$ ; Fig. 7; Fig. 8	-	320	-	ns





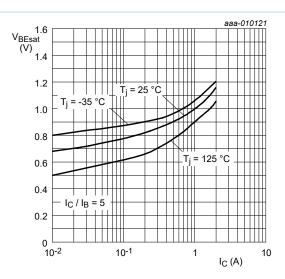


Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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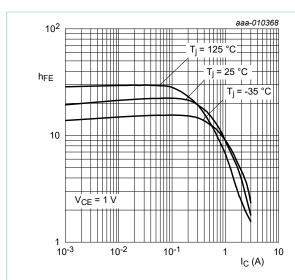


Fig. 5. DC current gain as a function of collector current; typical values

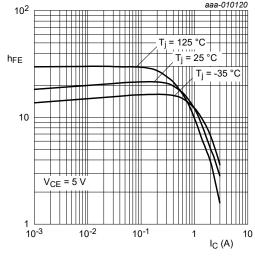


Fig. 6. DC current gain as a function of collector current; typical values

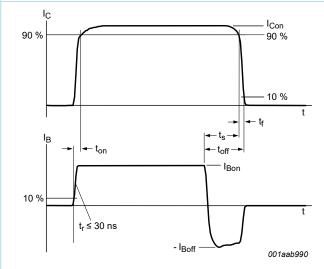
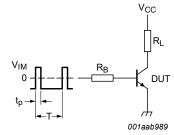


Fig. 7. Switching times waveforms for resistive load

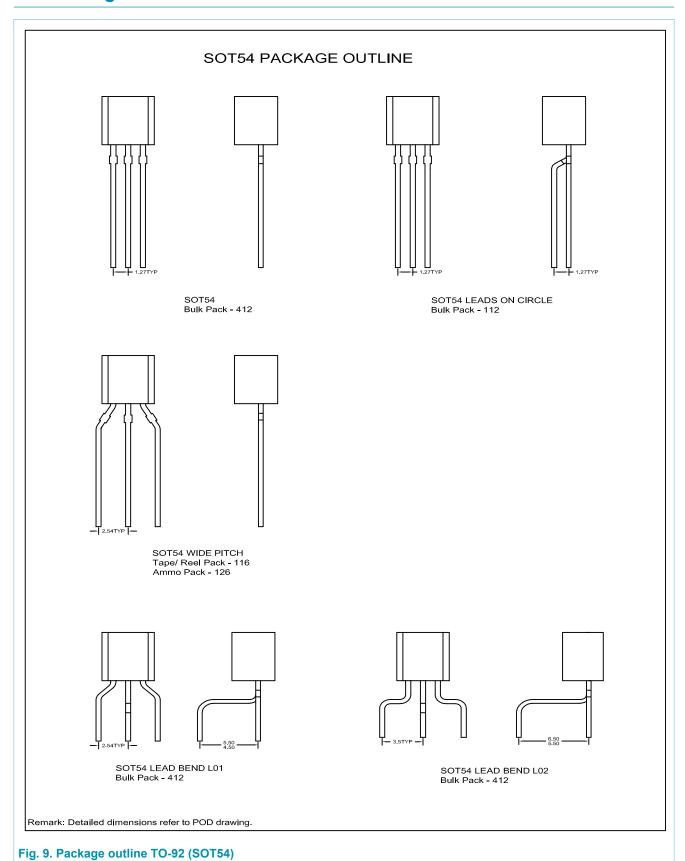


 $V_{IM}$  = -6 to +8 V;  $V_{CC}$  = 250 V;  $t_p$  = 20  $\mu$ s;  $\delta$  =  $\frac{t_p}{T}$  = 0.01 R<sub>B</sub> and R<sub>L</sub> calculated from  $I_{Con}$  and  $I_{Bon}$  requirements.

Fig. 8. Test circuit for resistive load switching

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# 10. Package outline



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## 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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